ABSTRACT OF THE DISCLOSURE

A photoresist or a residue of the photoresist may by removed by the hydrogen and water plasma mixture. The process may be performed at a temperature range between about 150°C and about 450°C, preferably about 250°C, and a power range between about 500 W and about 3000 W, preferably about 1400 W.

\IPL\DOCUMENTS\Appm\5735\PTO\Patent Application.doc